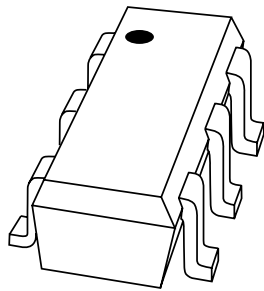


# DATA SHEET



## **PUMH4** NPN resistor-equipped double transistor

Product specification  
Supersedes data of 1998 Aug 10

1999 May 20

# NPN resistor-equipped double transistor

# PUMH4

### FEATURES

- Transistors with built-in bias resistor R1 (typ. 10 kΩ)
- No mutual interference between the transistors
- Simplification of circuit design
- Reduces number of components and board space.

### APPLICATIONS

- Especially suitable for space reduction in interface and driver circuits
- Inverter circuit configurations without use of external resistors.

### DESCRIPTION

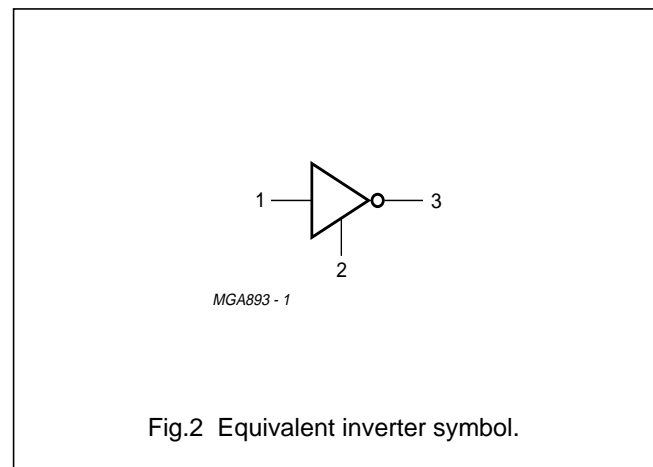
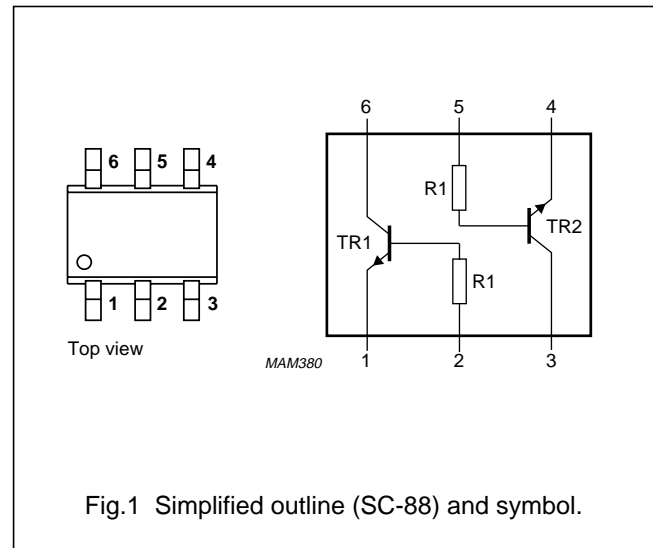
NPN resistor-equipped double transistor in an SC-88 (SOT363) plastic package.

### PINNING

| PIN  | DESCRIPTION        |
|------|--------------------|
| 1, 4 | emitter TR1; TR2   |
| 2, 5 | base TR1; TR2      |
| 6, 3 | collector TR1; TR2 |

### MARKING

| TYPE NUMBER | MARKING CODE |
|-------------|--------------|
| PUMH4       | Ht4          |



## NPN resistor-equipped double transistor

## PUMH4

## LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

| SYMBOL                | PARAMETER                     | CONDITIONS                       | MIN. | MAX. | UNIT |
|-----------------------|-------------------------------|----------------------------------|------|------|------|
| <b>Per transistor</b> |                               |                                  |      |      |      |
| V <sub>CBO</sub>      | collector-base voltage        | open emitter                     | –    | 50   | V    |
| V <sub>CEO</sub>      | collector-emitter voltage     | open base                        | –    | 50   | V    |
| V <sub>EBO</sub>      | emitter-base voltage          | open collector                   | –    | 5    | V    |
| I <sub>O</sub>        | output current (DC)           |                                  | –    | 100  | mA   |
| I <sub>CM</sub>       | peak collector current        |                                  | –    | 100  | mA   |
| P <sub>tot</sub>      | total power dissipation       | T <sub>amb</sub> ≤ 25 °C; note 1 | –    | 200  | mW   |
| T <sub>stg</sub>      | storage temperature           |                                  | –65  | +150 | °C   |
| T <sub>j</sub>        | junction temperature          |                                  | –    | 150  | °C   |
| T <sub>amb</sub>      | operating ambient temperature |                                  | –65  | +150 | °C   |
| <b>Per device</b>     |                               |                                  |      |      |      |
| P <sub>tot</sub>      | total power dissipation       | T <sub>amb</sub> ≤ 25 °C         | –    | 300  | mW   |

## Note

- Device mounted on an FR4 printed-circuit board.

## THERMAL CHARACTERISTICS

| SYMBOL              | PARAMETER                                   | CONDITIONS | VALUE | UNIT |
|---------------------|---|------------|-------|------|
| R <sub>th j-a</sub> | thermal resistance from junction to ambient | note 1     | 416   | K/W  |

## Note

- Device mounted on an FR4 printed-circuit board.

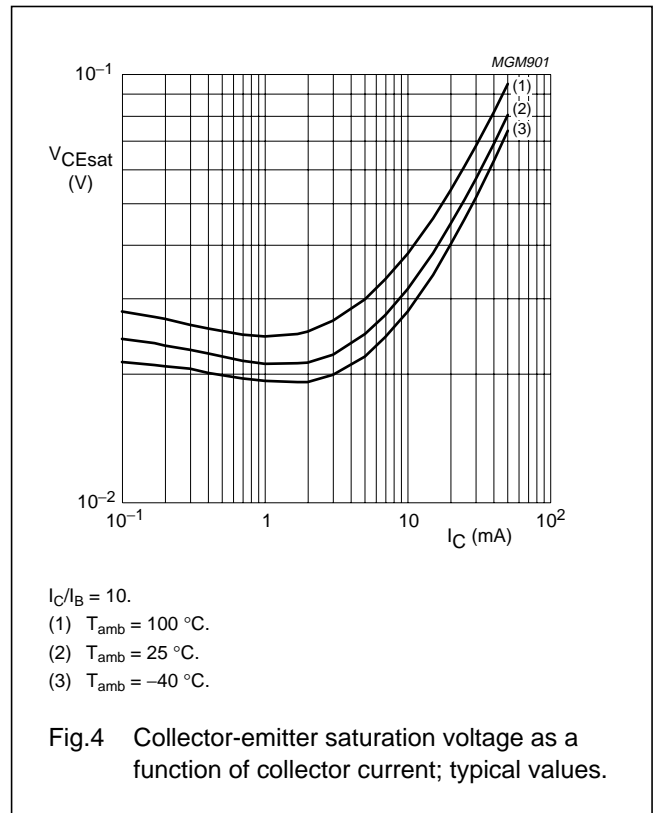
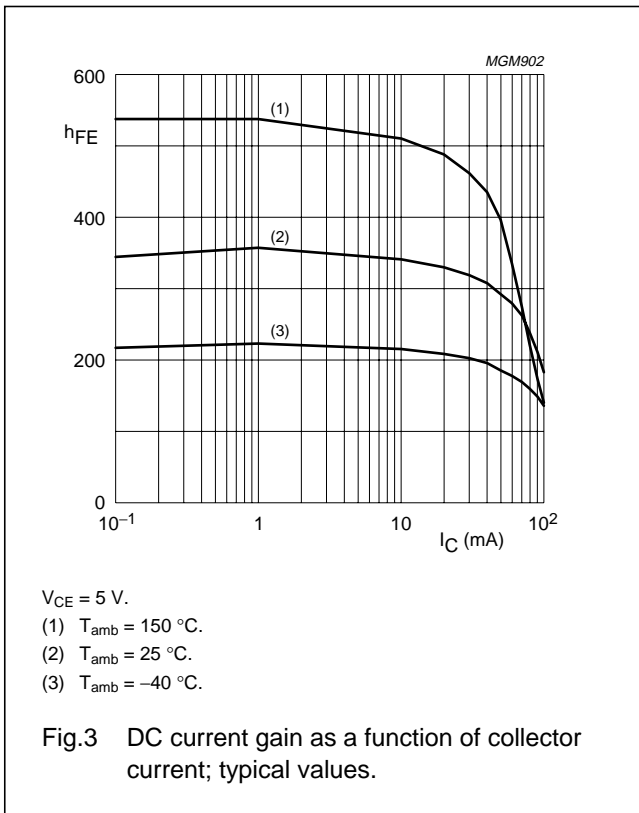
## CHARACTERISTICS

T<sub>amb</sub> = 25 °C unless otherwise specified.

| SYMBOL                | PARAMETER                            | CONDITIONS   | MIN. | TYP. | MAX. | UNIT |
|-----------------------|--------------------------------------|--|------|------|------|------|
| <b>Per transistor</b> |                                      |  |      |      |      |      |
| I <sub>CBO</sub>      | collector cut-off current            | I <sub>E</sub> = 0; V <sub>CB</sub> = 50 V                             | –    | –    | 100  | nA   |
| I <sub>CEO</sub>      | collector cut-off current            | I <sub>B</sub> = 0; V <sub>CE</sub> = 30 V                             | –    | –    | 1    | μA   |
|                       |                                      | I <sub>B</sub> = 0; V <sub>CE</sub> = 30 V; T <sub>j</sub> = 150 °C    | –    | –    | 50   | μA   |
| I <sub>EBO</sub>      | emitter cut-off current              | I <sub>C</sub> = 0; V <sub>EB</sub> = 5 V                              | –    | –    | 100  | nA   |
| h <sub>FE</sub>       | DC current gain                      | I <sub>C</sub> = 1 mA; V <sub>CE</sub> = 5 V                           | 200  | –    | –    |      |
| V <sub>CEsat</sub>    | collector-emitter saturation voltage | I <sub>C</sub> = 5 mA; I <sub>B</sub> = 0.25 mA                        | –    | –    | 150  | mV   |
| R1                    | input resistor                       |  | 7    | 10   | 13   | kΩ   |
| C <sub>c</sub>        | collector capacitance                | I <sub>E</sub> = I <sub>e</sub> = 0; V <sub>CB</sub> = 10 V; f = 1 MHz | –    | –    | 2.5  | pF   |

NPN resistor-equipped double transistor

PUMH4



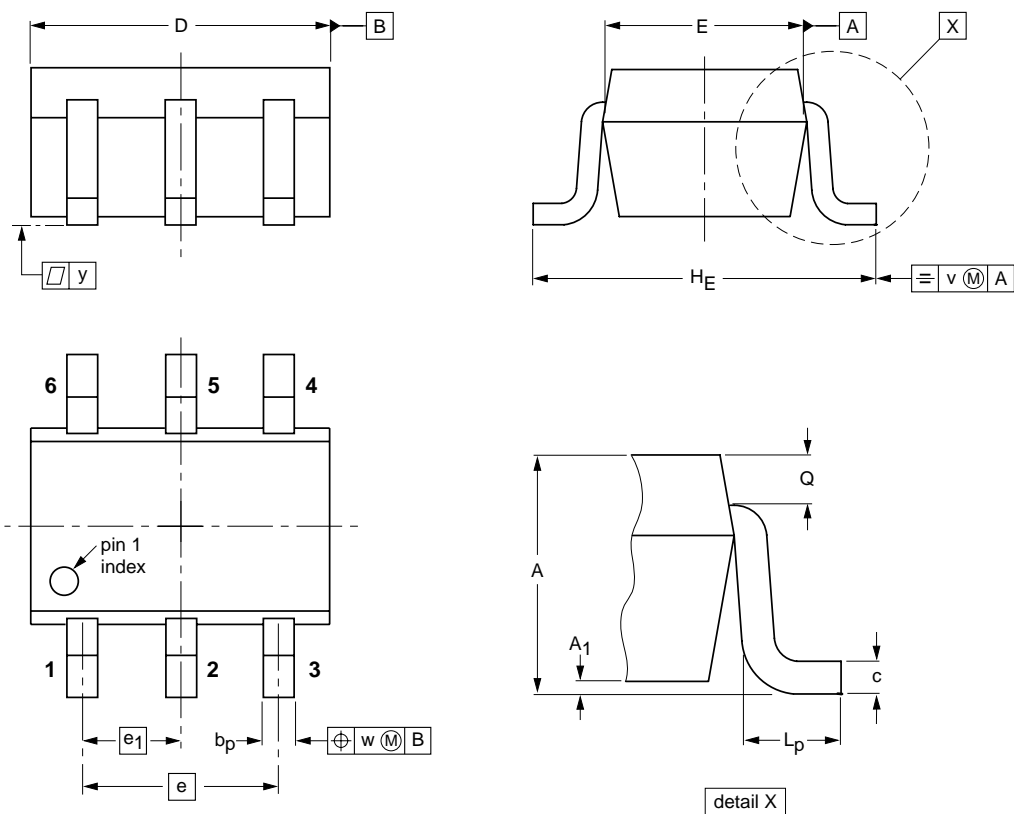
NPN resistor-equipped double transistor

PUMH4

PACKAGE OUTLINE

Plastic surface mounted package; 6 leads

SOT363



DIMENSIONS (mm are the original dimensions)

| UNIT | A          | A <sub>1</sub> max | b <sub>p</sub> | c            | D          | E            | e   | e <sub>1</sub> | H <sub>E</sub> | L <sub>p</sub> | Q            | v   | w   | y   |
|------|------------|--------------------|----------------|--------------|------------|--------------|-----|----------------|----------------|----------------|--------------|-----|-----|-----|
| mm   | 1.1<br>0.8 | 0.1                | 0.30<br>0.20   | 0.25<br>0.10 | 2.2<br>1.8 | 1.35<br>1.15 | 1.3 | 0.65           | 2.2<br>2.0     | 0.45<br>0.15   | 0.25<br>0.15 | 0.2 | 0.2 | 0.1 |

| OUTLINE VERSION | REFERENCES |       |       |  | EUROPEAN PROJECTION | ISSUE DATE |
|-----------------|------------|-------|-------|--|---------------------|------------|
|                 | IEC        | JEDEC | EIAJ  |  |                     |            |
| SOT363          |            |       | SC-88 |  |                     | 97-02-28   |

## NPN resistor-equipped double transistor

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**DEFINITIONS**

|   |   |
|---|---|
| <b>Data sheet status</b>  |   |
| Objective specification   | This data sheet contains target or goal specifications for product development.       |
| Preliminary specification   | This data sheet contains preliminary data; supplementary data may be published later. |
| Product specification   | This data sheet contains final product specifications.                                |
| <b>Limiting values</b>  |   |
| Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability. |   |
| <b>Application information</b>  |   |
| Where application information is given, it is advisory and does not form part of the specification.   |   |

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NPN resistor-equipped double transistor

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